

NX3DV2567

Low-ohmic four-pole double-throw analog switch

Rev. 2 — 9 November 2011

Product data sheet

1. General description

The NX3DV2567 is a four-pole double-throw analog switch (4PDT) optimized for switching WLAN-SIM supply, data and control signals. It has one digital select input (S) and four switches each with two independent input/outputs (nY0 and nY1) and a common input/output (nZ). Schmitt trigger action at S makes the circuit tolerant to slower input rise and fall times across the entire V_{CC} range from 1.4 V to 4.3 V.

A low input voltage threshold allows pin S to be driven by lower level logic signals without significant increase in supply current I_{CC} . This makes it possible for the NX3DV2567 to switch 4.3 V signals with a 1.8 V digital controller, eliminating the need for logic level translation.

The NX3DV2567 allows signals with amplitude up to V_{CC} to be transmitted from nZ to nY0 or nY1; or from nY0 or nY1 to nZ..

2. Features and benefits

- Wide supply voltage range from 1.4 V to 4.3 V
- Very low ON resistance for supply path:
 - ◆ 0.5 Ω (typical) at $V_{CC} = 1.8$ V
 - ◆ 0.45 Ω (typical) at $V_{CC} = 2.7$ V
- Low ON resistance for data path:
 - ◆ 7 Ω (typical) at $V_{CC} = 1.8$ V
 - ◆ 6 Ω (typical) at $V_{CC} = 2.7$ V
- Low ON capacitance for data path
- Wide -3 db bandwidth > 160 MHz
- Break-before-make switching
- High noise immunity
- ESD protection:
 - ◆ HBM JESD22-A114F Class 3A exceeds 4000 V
 - ◆ HBM JESD22-A114F Class 3A I/O to GND exceeds 7000 V
 - ◆ CDM AEC-Q100-011 revision B exceeds 1000 V
- CMOS low-power consumption
- Latch-up performance exceeds 100 mA per JESD 78B Class II Level A
- 1.8 V control logic at $V_{CC} = 3.6$ V
- Control input accepts voltages above supply voltage
- Very low supply current, even when input is below V_{CC}
- High current handling capability (350 mA continuous current under 3.3 V supply for supply path switch)



- Specified from $-40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$ and from $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$

3. Applications

- Cell phone, PDA, digital camera, printer and notebook
- LCD monitor, TV and set-top box

4. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
NX3DV2567HR	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	HXQFN16U	plastic thermal enhanced extremely thin quad flat package; no leads; 16 terminals; UTLP based; body $3 \times 3 \times 0.5\text{ mm}$	SOT1039-1
NX3DV2567GU	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	XQFN16	plastic, extremely thin quad flat package; no leads; 16 terminals; body $1.80 \times 2.60 \times 0.50\text{ mm}$	SOT1161-1

5. Marking

Table 2. Marking codes

Type number	Marking code
NX3DV2567HR	D60
NX3DV2567GU	D60

6. Functional diagram

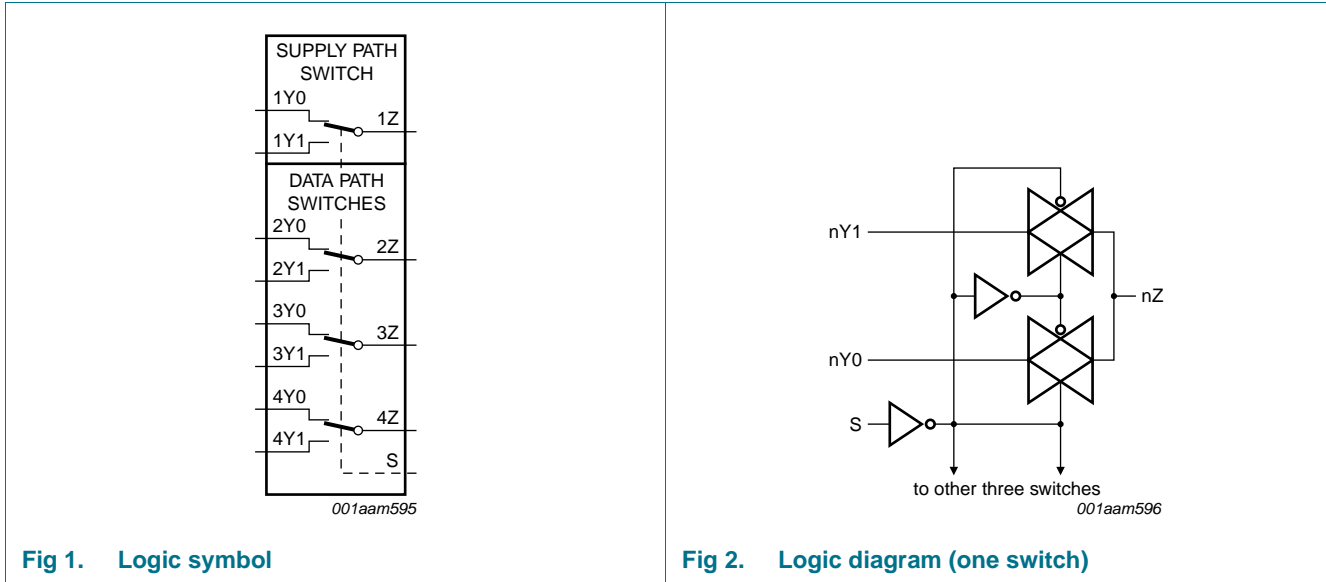


Fig 1. Logic symbol

Fig 2. Logic diagram (one switch)

7. Pinning information

7.1 Pinning

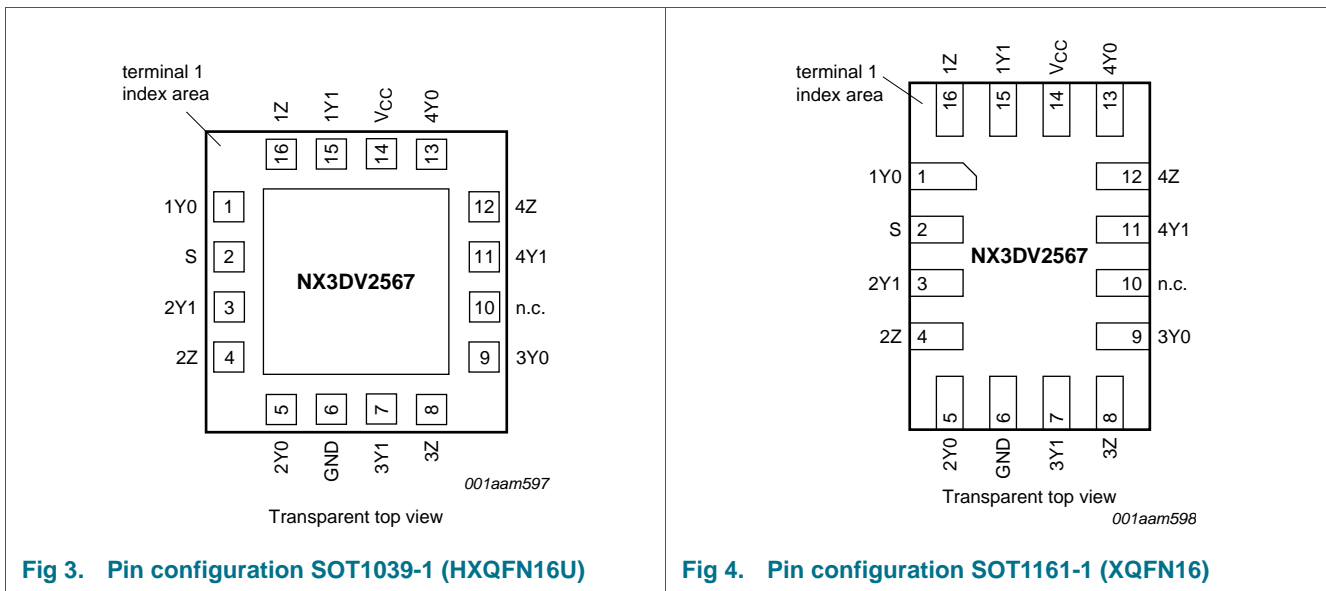


Fig 3. Pin configuration SOT1039-1 (HXQFN16U)

Fig 4. Pin configuration SOT1161-1 (XQFN16)

7.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
1Y0	1	independent input or output (supply switch)
2Y0, 3Y0, 4Y0	5, 9, 13	independent input or output (data switch)
S	2	select input
1Y1	15	independent input or output (supply switch)
2Y1, 3Y1, 4Y1	3, 7, 11	independent input or output (data switch)
1Z	16	common output or input (supply switch)
2Z, 3Z, 4Z	4, 8, 12	common output or input (data switch)
GND	6	ground (0 V)
n.c.	10	not connected
V _{CC}	14	supply voltage

8. Functional description

Table 4. Function table^[1]

Input S	Channel on
L	nY0
H	nY1

[1] H = HIGH voltage level; L = LOW voltage level.

9. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+4.6	V
V _I	input voltage	select input S	^[1] -0.5	+4.6	V
V _{SW}	switch voltage		^[2] -0.5	V _{CC} + 0.5	V
I _{IK}	input clamping current	V _I < -0.5 V	-50	-	mA
I _{SK}	switch clamping current	V _I < -0.5 V or V _I > V _{CC} + 0.5 V	-	±50	mA
I _{SW}	switch current	supply path switch			
		V _{SW} > -0.5 V or V _{SW} < V _{CC} + 0.5 V; source or sink current	-	±350	mA
		V _{SW} > -0.5 V or V _{SW} < V _{CC} + 0.5 V; pulsed at 1 ms duration, < 10 % duty cycle; peak current	-	±500	mA
		data path switch			
		V _{SW} > -0.5 V or V _{SW} < V _{CC} + 0.5 V; source or sink current	-	±128	mA
T _{stg}	storage temperature		-65	+150	°C

Table 5. Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
P _{tot}	total power dissipation	T _{amb} = -40 °C to +125 °C	[3][4] -	250	mW

- [1] The minimum input voltage rating may be exceeded if the input current rating is observed.
- [2] The minimum and maximum switch voltage ratings may be exceeded if the switch clamping current rating is observed but may not exceed 4.6 V.
- [3] For HXQFN16U package: above 135 °C the value of P_{tot} derates linearly with 16.9 mW/K.
- [4] For XQFN16 package: above 133 °C the value of P_{tot} derates linearly with 14.5 mW/K.

10. Recommended operating conditions

Table 6. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		1.4	4.3	V
V _I	input voltage	select input S	0	4.3	V
V _{SW}	switch voltage		[1] 0	V _{CC}	V
T _{amb}	ambient temperature		-40	+125	°C
Δt/ΔV	input transition rise and fall rate	V _{CC} = 1.4 V to 4.3 V	[2] -	200	ns/V

- [1] To avoid sinking GND current from terminal nZ when switch current flows in terminal nYn, the voltage drop across the bidirectional switch must not exceed 0.4 V. If the switch current flows into terminal nZ, no GND current will flow from terminal nYn. In this case, there is no limit for the voltage drop across the switch.
- [2] Applies to control signal levels.

11. Static characteristics

Table 7. Static characteristics

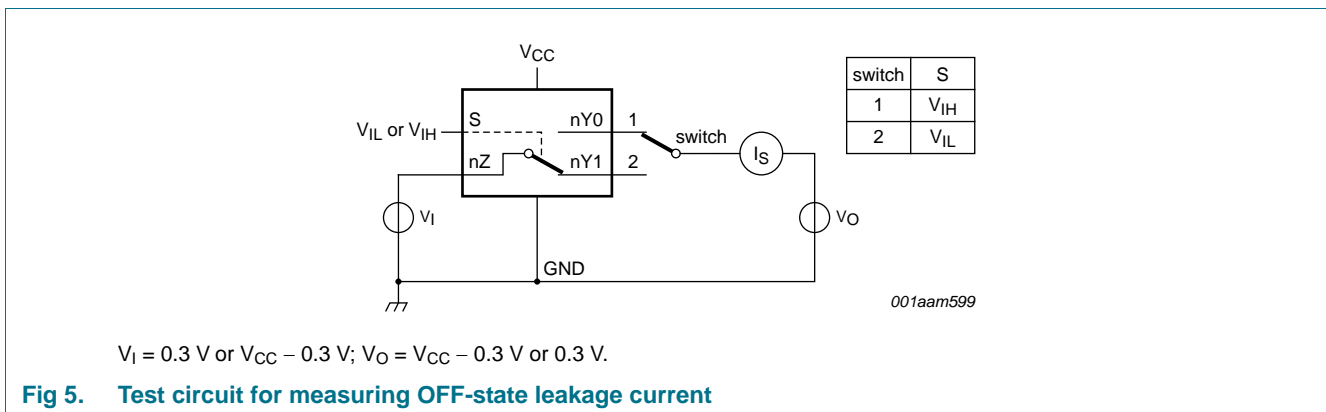
At recommended operating conditions; voltages are referenced to GND (ground 0 V).

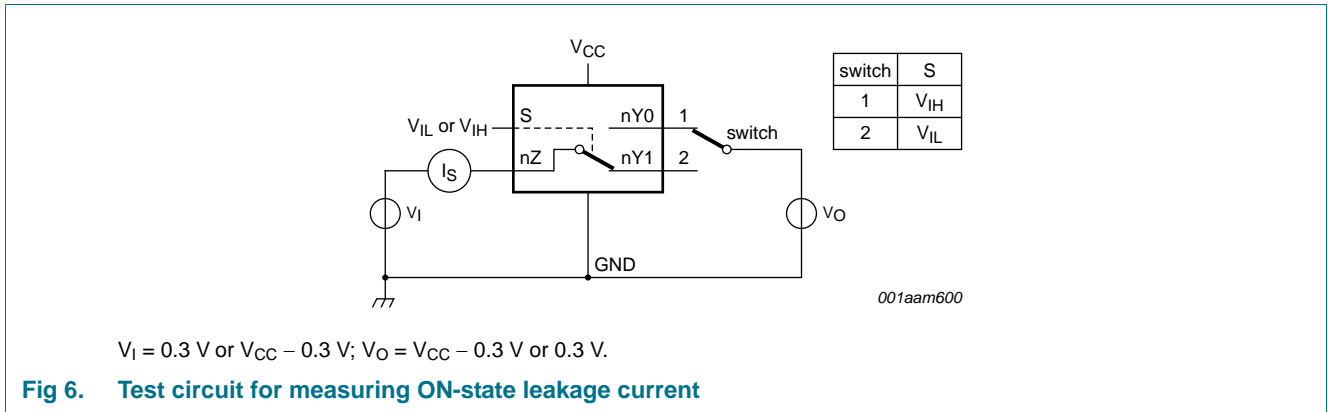
Symbol	Parameter	Conditions	T _{amb} = 25 °C			T _{amb} = -40 °C to +125 °C			Unit
			Min	Typ	Max	Min	Max (85 °C)	Max (125 °C)	
V _{IH}	HIGH-level input voltage	V _{CC} = 1.4 V to 1.6 V	0.9	-	-	0.9	-	-	V
		V _{CC} = 1.65 V to 1.95 V	0.9	-	-	0.9	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.1	-	-	1.1	-	-	V
		V _{CC} = 2.7 V to 3.6 V	1.3	-	-	1.3	-	-	V
		V _{CC} = 3.6 V to 4.3 V	1.4	-	-	1.4	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 1.4 V to 1.6 V	-	-	0.3	-	0.3	0.3	V
		V _{CC} = 1.65 V to 1.95 V	-	-	0.4	-	0.4	0.3	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.4	-	0.4	0.4	V
		V _{CC} = 2.7 V to 3.6 V	-	-	0.5	-	0.5	0.5	V
		V _{CC} = 3.6 V to 4.3 V	-	-	0.6	-	0.6	0.6	V
I _I	input leakage current	select input S; V _I = GND to 4.3 V; V _{CC} = 1.4 V to 4.3 V	-	-	-	-	±0.5	±1	μA

Table 7. Static characteristics ...continued
 At recommended operating conditions; voltages are referenced to GND (ground 0 V).

Symbol	Parameter	Conditions	T _{amb} = 25 °C			T _{amb} = -40 °C to +125 °C			Unit
			Min	Typ	Max	Min	Max (85 °C)	Max (125 °C)	
I _{S(OFF)}	OFF-state leakage current	nY0 and nY1 port; see Figure 5							
		V _{CC} = 1.4 V to 3.6 V	-	-	±5	-	±50	±500	nA
		V _{CC} = 3.6 V to 4.3 V	-	-	±10	-	±50	±500	nA
I _{S(ON)}	ON-state leakage current	nZ port; V _{CC} = 1.4 V to 3.6 V; see Figure 6							
		V _{CC} = 1.4 V to 3.6 V	-	-	±5	-	±50	±500	nA
		V _{CC} = 3.6 V to 4.3 V	-	-	±10	-	±50	±500	nA
I _{CC}	supply current	V _I = V _{CC} or GND; V _{SW} = GND or V _{CC}							
		V _{CC} = 3.6 V	-	-	100	-	500	5000	nA
		V _{CC} = 4.3 V	-	-	150	-	800	6000	nA
ΔI _{CC}	additional supply current	V _{SW} = GND or V _{CC}							
		V _I = 2.6 V; V _{CC} = 4.3 V	-	2.0	4.0	-	7	7	μA
		V _I = 2.6 V; V _{CC} = 3.6 V	-	0.35	0.7	-	1	1	μA
		V _I = 1.8 V; V _{CC} = 4.3 V	-	7.0	10.0	-	15	15	μA
		V _I = 1.8 V; V _{CC} = 3.6 V	-	2.5	4.0	-	5	5	μA
		V _I = 1.8 V; V _{CC} = 2.5 V	-	50	200	-	300	500	nA
C _I	input capacitance		-	1	-	-	-	-	pF
C _{S(OFF)}	OFF-state capacitance	supply path switch	-	35	-	-	-	-	pF
		data path switch	-	3	-	-	-	-	pF
C _{S(ON)}	ON-state capacitance	supply path switch	-	130	-	-	-	-	pF
		data path switch	-	16	-	-	-	-	pF

11.1 Test circuits





11.2 ON resistance

Table 8. ON resistance

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); for graphs see [Figure 8](#) to [Figure 13](#).

Symbol	Parameter	Conditions	T _{amb} = -40 °C to +85 °C			T _{amb} = -40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
Supply path switch								
R _{ON}	ON resistance	V _I = GND to V _{CC} ; I _{SW} = 100 mA; see Figure 7						
		V _{CC} = 1.8 V; V _{SW} = 0 V, 1.8 V	-	0.5	0.75	-	0.85	Ω
		V _{CC} = 2.7 V; V _{SW} = 0 V, 2.3 V	-	0.45	0.7	-	0.8	Ω
ΔR _{ON}	ON resistance mismatch between channels	V _I = GND to V _{CC} ; I _{SW} = 100 mA ^[2] V _{CC} = 2.7 V; V _{SW} = 0 V	-	0.1	-	-	-	Ω
Data path switches								
R _{ON}	ON resistance	V _I = GND to V _{CC} ; I _{SW} = 20 mA; see Figure 7						
		V _{CC} = 1.8 V; V _{SW} = 0 V, 1.8 V	-	7.0	10.0	-	11.0	Ω
		V _{CC} = 2.7 V; V _{SW} = 0 V, 2.3 V	-	6.0	9.5	-	10.5	Ω
ΔR _{ON}	ON resistance mismatch between channels	V _I = GND to V _{CC} ; I _{SW} = 20 mA ^[2] V _{CC} = 2.7 V; V _{SW} = 0 V	-	0.2	-	-	-	Ω

[1] Typical values are measured at T_{amb} = 25 °C.

[2] Measured at identical V_{CC}, temperature and input voltage.

11.3 ON resistance test circuit and graphs

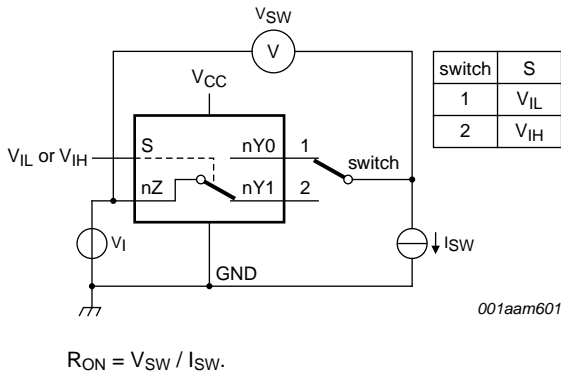
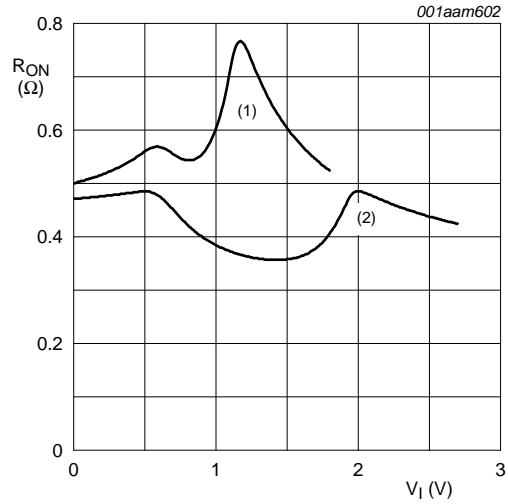
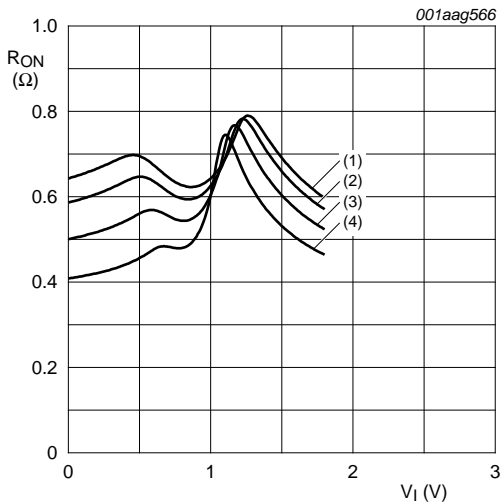


Fig 7. Test circuit for measuring ON resistance



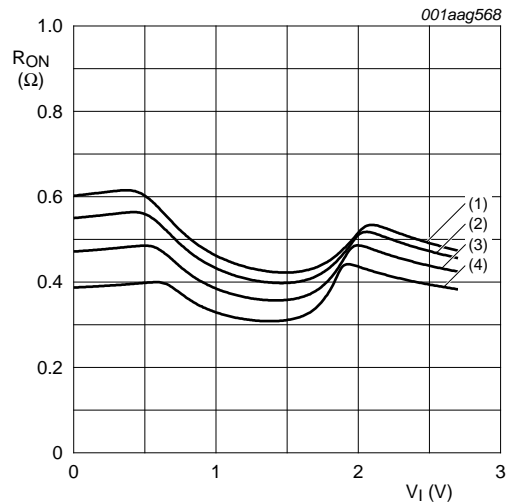
- (1) V_{CC} = 1.8 V.
- (2) V_{CC} = 2.7 V.

Fig 8. Typical ON resistance as a function of input voltage (supply path switch)



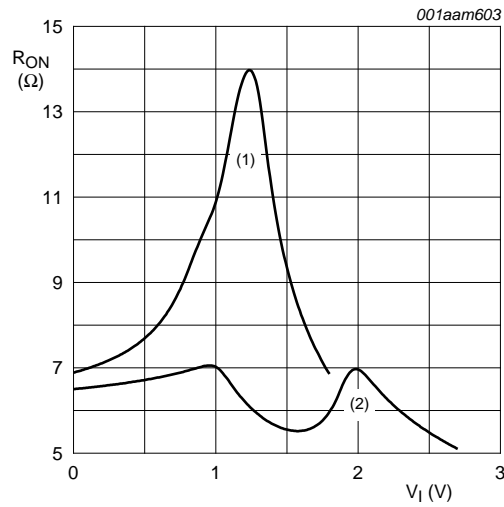
- (1) T_{amb} = 125 °C.
- (2) T_{amb} = 85 °C.
- (3) T_{amb} = 25 °C.
- (4) T_{amb} = -40 °C.

Fig 9. ON resistance as a function of input voltage; V_{CC} = 1.8 V (supply path switch)



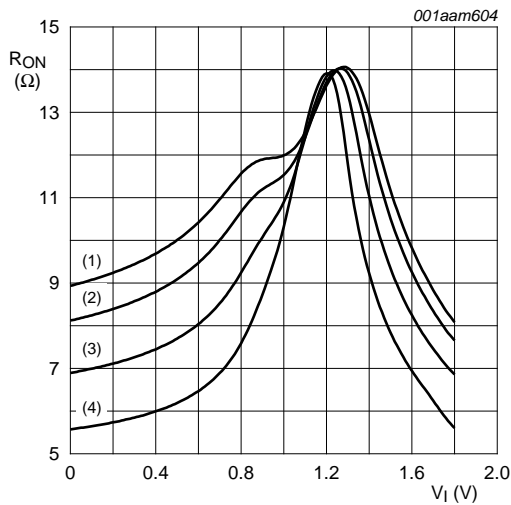
- (1) T_{amb} = 125 °C.
- (2) T_{amb} = 85 °C.
- (3) T_{amb} = 25 °C.
- (4) T_{amb} = -40 °C.

Fig 10. ON resistance as a function of input voltage; V_{CC} = 2.7 V (supply path switch)



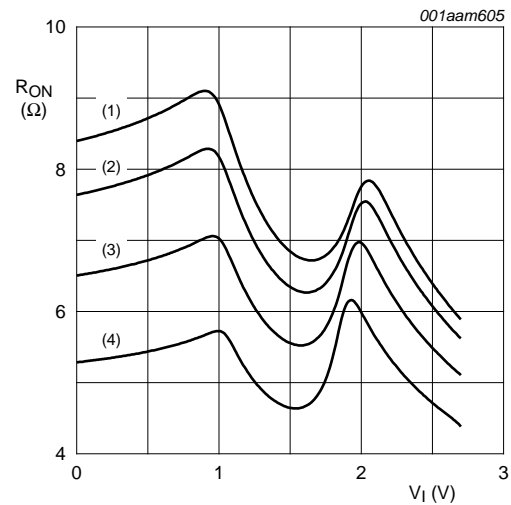
- (1) $V_{CC} = 1.8 \text{ V}$.
- (2) $V_{CC} = 2.7 \text{ V}$.

Fig 11. Typical ON resistance as a function of input voltage (data path switch)



- (1) $T_{amb} = 125 \text{ }^\circ\text{C}$.
- (2) $T_{amb} = 85 \text{ }^\circ\text{C}$.
- (3) $T_{amb} = 25 \text{ }^\circ\text{C}$.
- (4) $T_{amb} = -40 \text{ }^\circ\text{C}$.

Fig 12. ON resistance as a function of input voltage; $V_{CC} = 1.8 \text{ V}$ (data path switch)



- (1) $T_{amb} = 125 \text{ }^\circ\text{C}$.
- (2) $T_{amb} = 85 \text{ }^\circ\text{C}$.
- (3) $T_{amb} = 25 \text{ }^\circ\text{C}$.
- (4) $T_{amb} = -40 \text{ }^\circ\text{C}$.

Fig 13. ON resistance as a function of input voltage; $V_{CC} = 2.7 \text{ V}$ (data path switch)

12. Dynamic characteristics

Table 9. Dynamic characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); for load circuit see [Figure 16](#).

Symbol	Parameter	Conditions	25 °C			-40 °C to +125 °C			Unit
			Min	Typ ^[1]	Max	Min	Max (85 °C)	Max (125 °C)	
Supply path switch									
t _{en}	enable time	S to 1Z or 1Y0, 1Y1; see Figure 14							
		V _{CC} = 1.4 V to 1.6 V	-	41	90	-	120	120	ns
		V _{CC} = 1.65 V to 1.95 V	-	30	70	-	80	90	ns
		V _{CC} = 2.3 V to 2.7 V	-	20	45	-	50	55	ns
		V _{CC} = 2.7 V to 3.6 V	-	19	40	-	45	50	ns
		V _{CC} = 3.6 V to 4.3 V	-	19	40	-	45	50	ns
t _{dis}	disable time	S to 1Z or 1Y0, 1Y1; see Figure 14							
		V _{CC} = 1.4 V to 1.6 V	-	24	70	-	80	90	ns
		V _{CC} = 1.65 V to 1.95 V	-	15	55	-	60	65	ns
		V _{CC} = 2.3 V to 2.7 V	-	9	25	-	30	35	ns
		V _{CC} = 2.7 V to 3.6 V	-	8	20	-	25	30	ns
		V _{CC} = 3.6 V to 4.3 V	-	8	20	-	25	30	ns
t _{b-m}	break-before-make time	see Figure 15							
		[2]							
		V _{CC} = 1.4 V to 1.6 V	-	20	-	9	-	-	ns
		V _{CC} = 1.65 V to 1.95 V	-	17	-	7	-	-	ns
		V _{CC} = 2.3 V to 2.7 V	-	13	-	4	-	-	ns
		V _{CC} = 2.7 V to 3.6 V	-	11	-	3	-	-	ns
		V _{CC} = 3.6 V to 4.3 V	-	11	-	2	-	-	ns
Data path switch									
t _{en}	enable time	S to nZ or nYn; see Figure 14							
		V _{CC} = 1.4 V to 1.6 V	-	40	90	-	120	120	ns
		V _{CC} = 1.65 V to 1.95 V	-	29	70	-	80	90	ns
		V _{CC} = 2.3 V to 2.7 V	-	20	45	-	50	55	ns
		V _{CC} = 2.7 V to 3.6 V	-	19	40	-	45	50	ns
		V _{CC} = 3.6 V to 4.3 V	-	19	40	-	45	50	ns
t _{dis}	disable time	S to nZ or nYn; see Figure 14							
		V _{CC} = 1.4 V to 1.6 V	-	21	70	-	80	90	ns
		V _{CC} = 1.65 V to 1.95 V	-	13	55	-	60	65	ns
		V _{CC} = 2.3 V to 2.7 V	-	8	25	-	30	35	ns
		V _{CC} = 2.7 V to 3.6 V	-	7	20	-	25	30	ns
		V _{CC} = 3.6 V to 4.3 V	-	7	20	-	25	30	ns

Table 9. Dynamic characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); for load circuit see [Figure 16](#).

Symbol	Parameter	Conditions	25 °C			-40 °C to +125 °C			Unit
			Min	Typ ^[1]	Max	Min	Max (85 °C)	Max (125 °C)	
t_{b-m}	break-before-make time	see Figure 15 ^[2]							
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$	-	23	-	9	-	-	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	-	19	-	7	-	-	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	-	15	-	4	-	-	ns
		$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$	-	13	-	3	-	-	ns
		$V_{CC} = 3.6 \text{ V to } 4.3 \text{ V}$	-	12	-	2	-	-	ns

[1] Typical values are measured at $T_{amb} = 25 \text{ °C}$ and $V_{CC} = 1.5 \text{ V}, 1.8 \text{ V}, 2.5 \text{ V}, 3.3 \text{ V}$ and 4.3 V respectively.

[2] Break-before-make guaranteed by design.

12.1 Waveform and test circuits

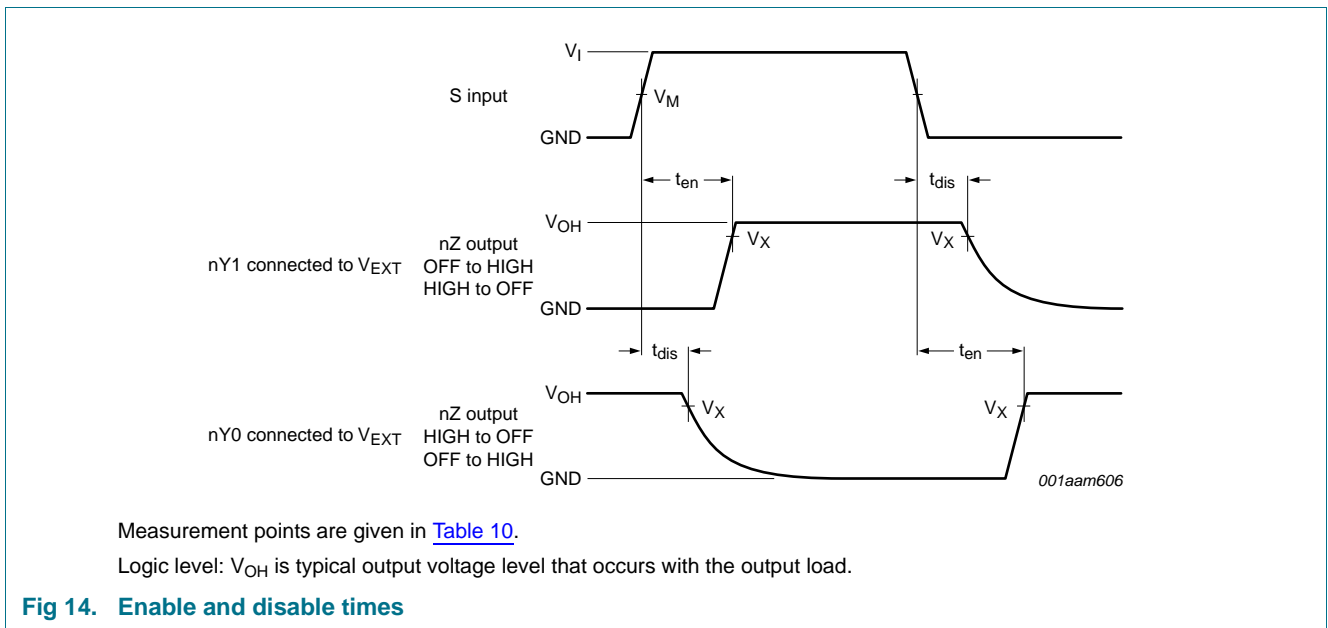


Table 10. Measurement points

Supply voltage	Input	Output
V_{CC}	V_M	V_X
1.4 V to 4.3 V	$0.5V_{CC}$	$0.9V_{OH}$

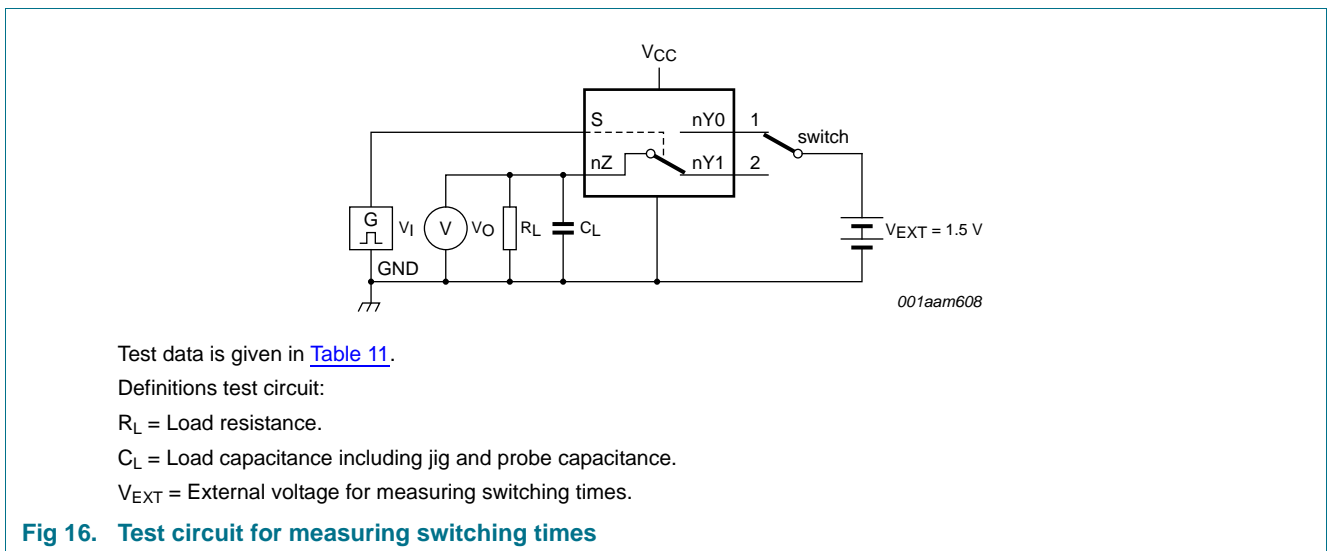
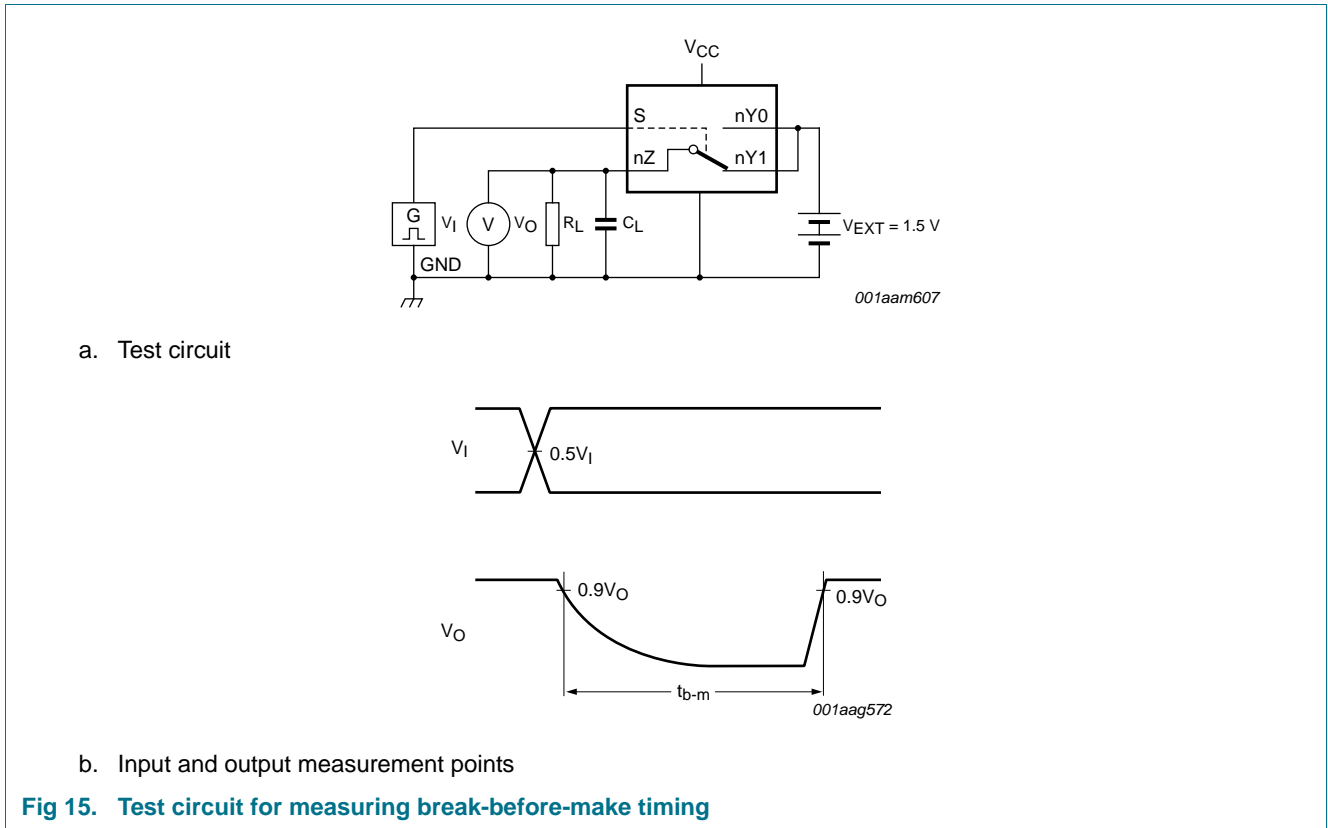


Table 11. Test data

Supply voltage	Input		Load	
V_{CC}	V_I	t_r, t_f	C_L	R_L
1.4 V to 4.3 V	V_{CC}	≤ 2.5 ns	35 pF	50 Ω

12.2 Additional dynamic characteristics

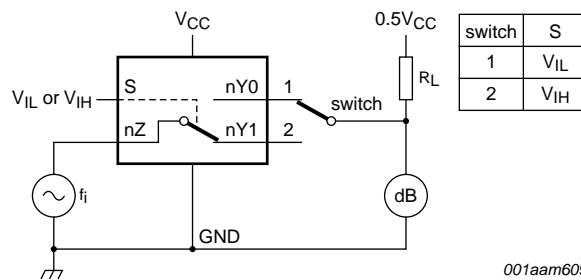
Table 12. Additional dynamic characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); $V_I = \text{GND}$ or V_{CC} (unless otherwise specified); $t_r = t_f \leq 2.5 \text{ ns}$; $T_{amb} = 25 \text{ }^\circ\text{C}$.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Data path switch						
$f_{(-3\text{dB})}$	-3 dB frequency response	$R_L = 50 \text{ } \Omega$; see Figure 17 $V_{CC} = 2.7 \text{ V}$ to 3.6 V	[1]	-	330	MHz
α_{iso}	isolation (OFF-state)	$f_i = 10 \text{ MHz}$; $R_L = 50 \text{ } \Omega$; see Figure 18 $V_{CC} = 2.7 \text{ V}$ to 3.6 V	[1]	-	-60	dB
Xtalk	crosstalk	between switches; $f_i = 10 \text{ MHz}$; $R_L = 50 \text{ } \Omega$; see Figure 19 $V_{CC} = 2.7 \text{ V}$ to 3.6 V	[1]	-	-60	dB
Q_{inj}	charge injection	$f_i = 1 \text{ MHz}$; $C_L = 0.1 \text{ nF}$; $R_L = 1 \text{ M}\Omega$; $V_{\text{gen}} = 0 \text{ V}$; $R_{\text{gen}} = 0 \text{ } \Omega$; see Figure 20 $V_{CC} = 2.7 \text{ V}$ to 3.6 V	-	10	-	pC

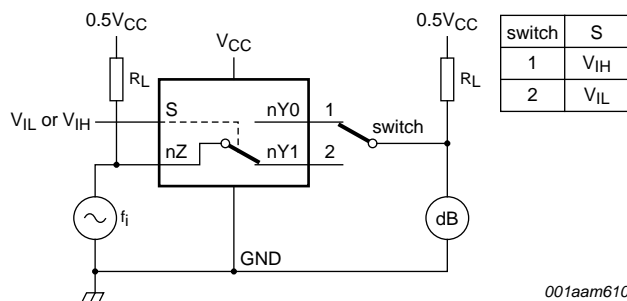
[1] f_i is biased at $0.5V_{CC}$.

12.3 Test circuits



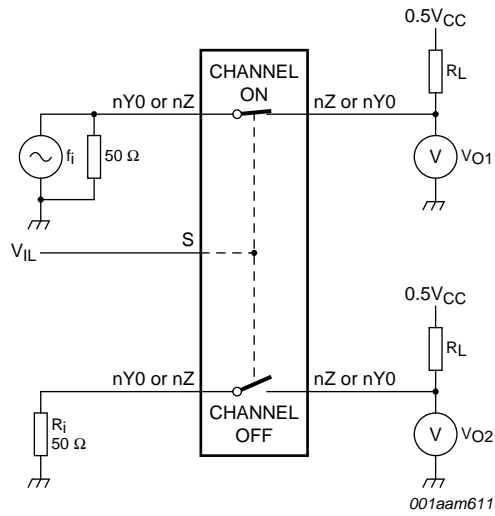
Adjust f_i voltage to obtain 0 dBm level at output. Increase f_i frequency until dB meter reads -3 dB.

Fig 17. Test circuit for measuring the frequency response when channel is in ON-state



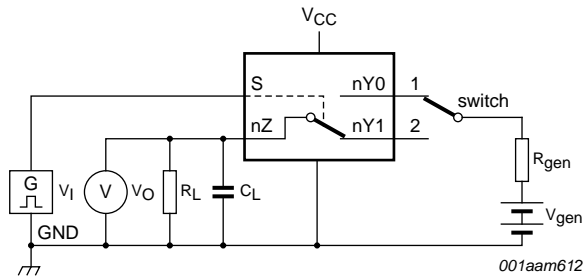
Adjust f_i voltage to obtain 0 dBm level at input.

Fig 18. Test circuit for measuring isolation (OFF-state)

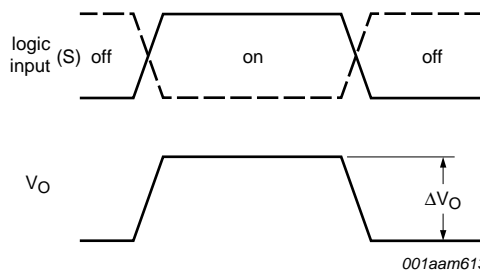


$20 \log_{10} (V_{O2} / V_{O1})$ or $20 \log_{10} (V_{O1} / V_{O2})$.

Fig 19. Test circuit for measuring crosstalk between switches



a. Test circuit



b. Input and output pulse definitions

Definition: $Q_{inj} = \Delta V_O \times C_L$.

ΔV_O = output voltage variation.

R_{gen} = generator resistance.

V_{gen} = generator voltage.

Fig 20. Test circuit for measuring charge injection

13. Package outline

HXQFN16U: plastic thermal enhanced extremely thin quad flat package; no leads; 16 terminals; UTLP based; body 3 x 3 x 0.5 mm

SOT1039-1

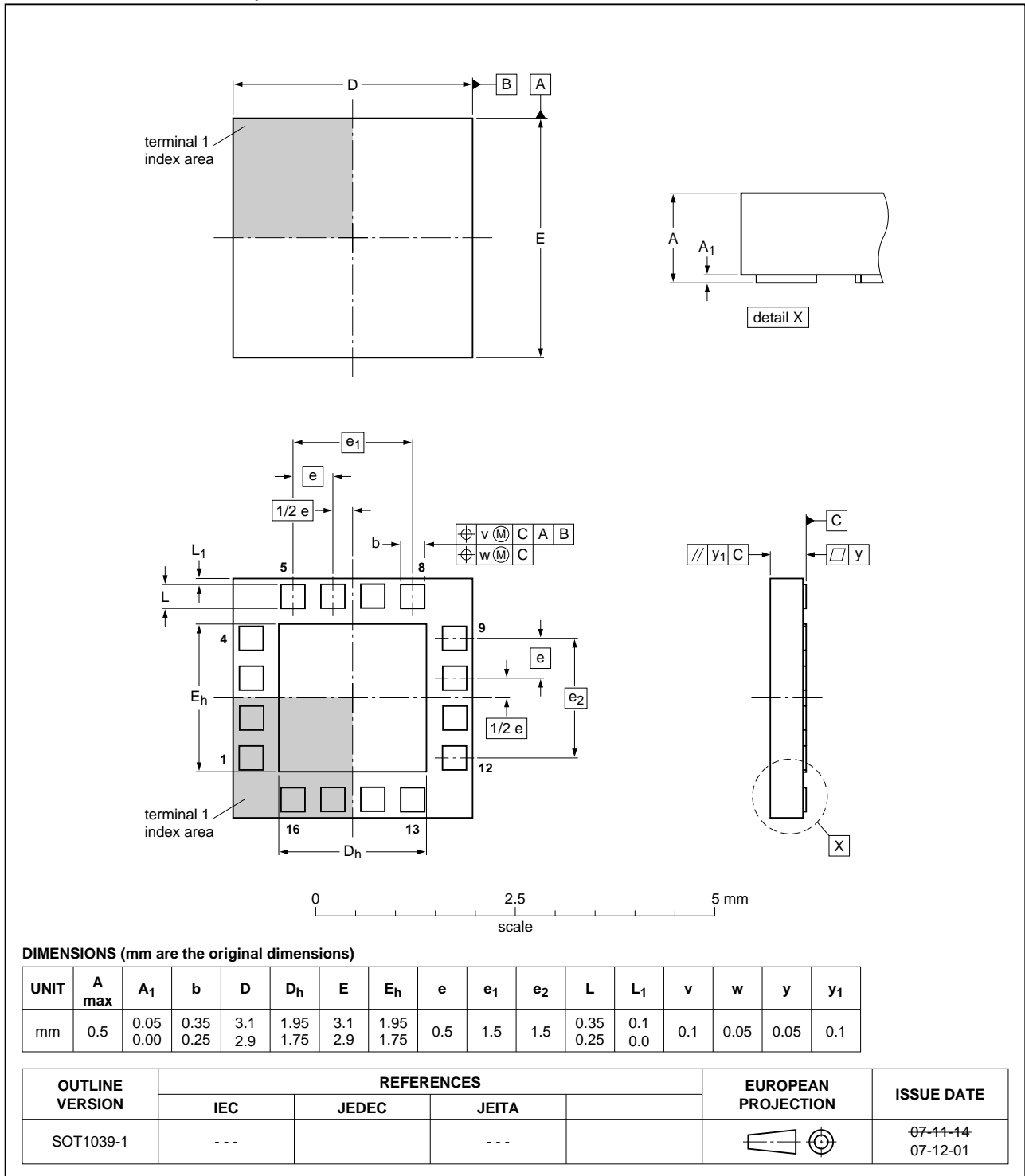


Fig 21. Package outline SOT1039-1 (HXQFN16U)

XQFN16: plastic, extremely thin quad flat package; no leads; 16 terminals; body 1.80 x 2.60 x 0.50 mm

SOT1161-1

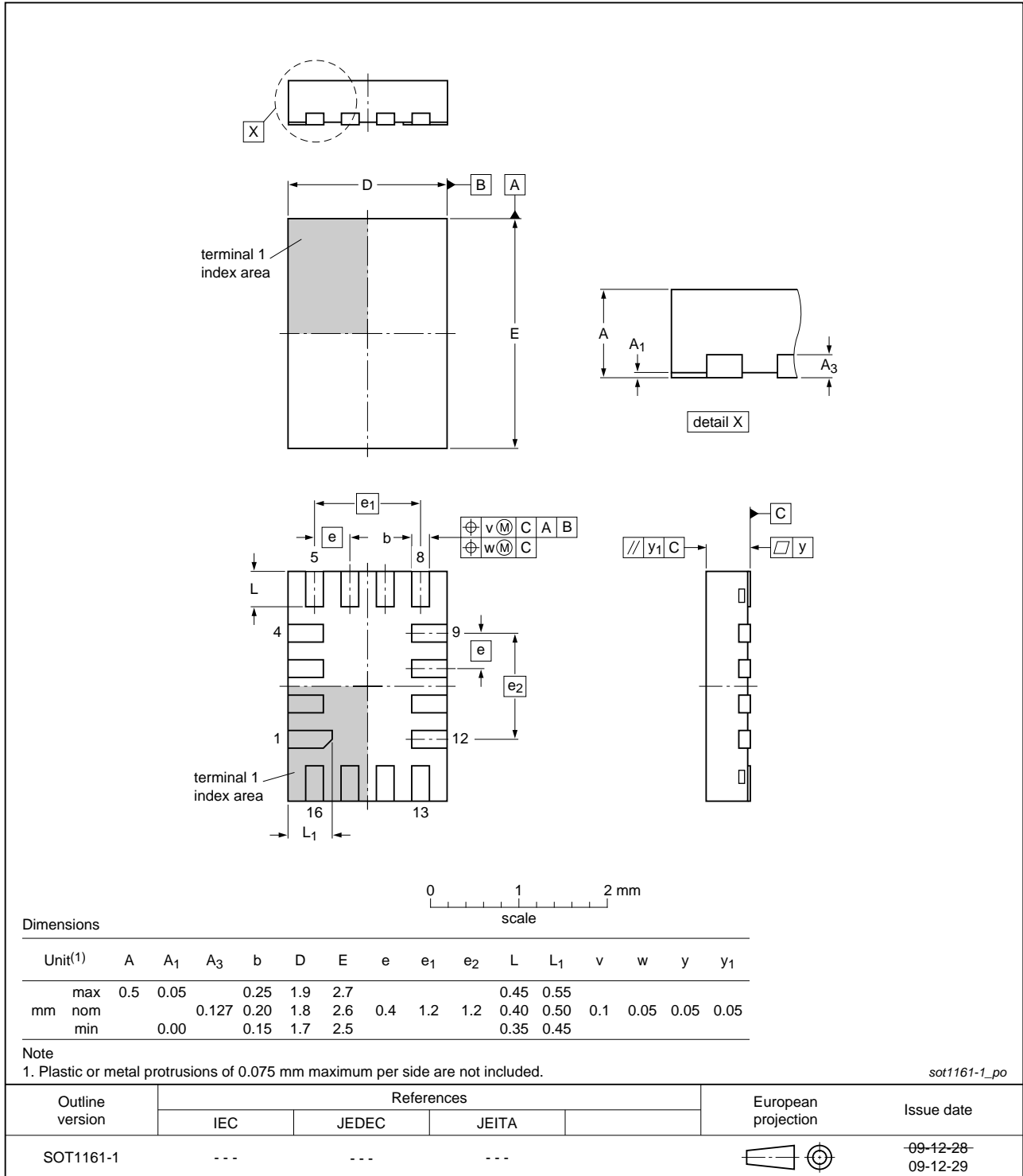


Fig 22. Package outline SOT1161-1 (XQFN16)

14. Abbreviations

Table 13. Abbreviations

Acronym	Description
CDM	Charged Device Model
CMOS	Complementary Metal-Oxide Semiconductor
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
PDA	Personal Digital Assistant
TTL	Transistor-Transistor Logic

15. Revision history

Table 14. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
NX3DV2567 v.2	20111109	Product data sheet	-	NX3DV2567 v.1
Modifications:	<ul style="list-style-type: none">• Legal pages updated.			
NX3DV2567 v.1	20100928	Product data sheet	-	-

16. Legal information

16.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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18. Contents

1	General description	1
2	Features and benefits	1
3	Applications	2
4	Ordering information	2
5	Marking	2
6	Functional diagram	3
7	Pinning information	3
7.1	Pinning	3
7.2	Pin description	4
8	Functional description	4
9	Limiting values	4
10	Recommended operating conditions	5
11	Static characteristics	5
11.1	Test circuits	6
11.2	ON resistance	7
11.3	ON resistance test circuit and graphs	8
12	Dynamic characteristics	10
12.1	Waveform and test circuits	11
12.2	Additional dynamic characteristics	13
12.3	Test circuits	13
13	Package outline	15
14	Abbreviations	17
15	Revision history	17
16	Legal information	18
16.1	Data sheet status	18
16.2	Definitions	18
16.3	Disclaimers	18
16.4	Trademarks	19
17	Contact information	19
18	Contents	20

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Как с нами связаться

Телефон: 8 (812) 309 58 32 (многоканальный)

Факс: 8 (812) 320-02-42

Электронная почта: org@eplast1.ru

Адрес: 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.